



HY11P32

Datasheet

8-Bit RISC-Like Mixed Signal Microcontroller
Embedded 4x12 LCD Driver
18-Bit Σ ADC

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1. Features

- 8-bit RISC, 46 instructions included.
- Operating voltage range: 2.2V to 3.6V, operation temperature range: -40°C~85°C.
- External Crystal Oscillator and Internal High Precision RC Oscillator, 6 CPU clock rates enable users to have the most power-saving plan.
 - Active Mode 300uA@2MHz
 - Standby Mode 3uA@28KHz
 - Sleep Mode 1uA
- 2K Word OTP (One Time Programmable) Type Program Memory, 128 Byte Data Memory
- Brownout detector and Watch dog Timer, prevents CPU from Crash.
- 18-bit fully differential input Sigma-Delta Analog-to-Digital Converter (A/D)
 - Built-in PGA (Programmable Gain Amplifier) 1/4x、1/2x、1x...128x、10 input signal gain selection.
 - Built-in Input zero point adjustment can increase measurement range according to different application.
- 1.0V internal analog circuit common ground that equips with Push-Pull drive ability to provide sensor driving voltage.
- LVD low voltage detection function has 14 steps of voltage detection configuration and external input voltage detection function.
- Analog voltage source, VDDA equips with 10mA low dropout regulator function
- 4x12 LCD Driver
 - 1/4 Duty, 1/3 Bias
 - Built-in Charge Pump regulated circuit, providing 4 LCD Bias voltage
- 8-bit Timer A
- Built-in EPROM (BIE)
- Support 6 stack level

2. Pin Definition

2.1 PIN Diagram LQFP44

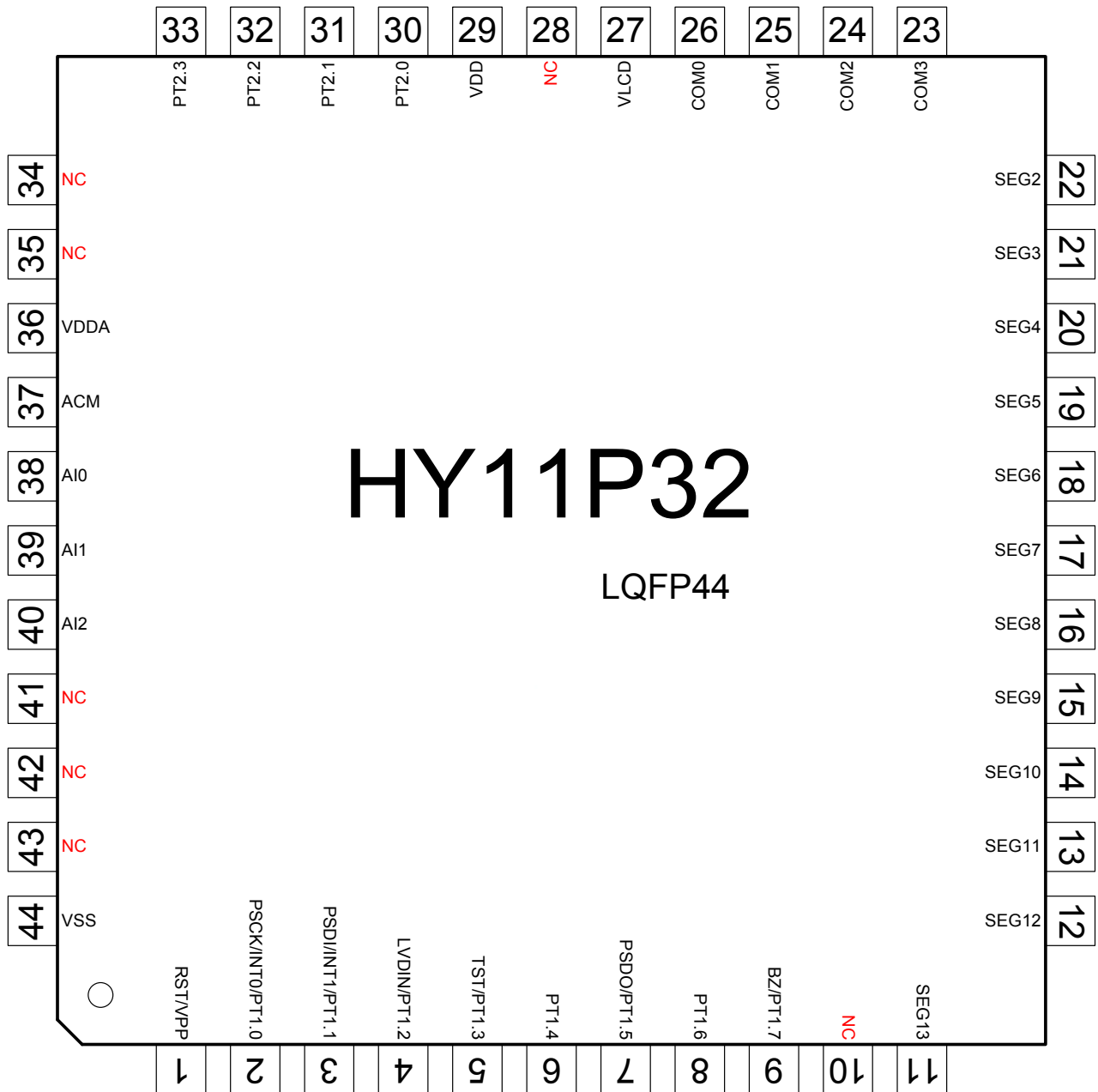


Figure 2-1 HY11P32 LQFP44 Pin Diagram

Note 1 : VPP and RST use the same pin. Input voltage cannot exceed 5.8V when not programming EPROM.

Note 2 : TST and PT1.3 use the same pin. Input voltage cannot exceed Vdd+0.3V while operating.

Note 3 : If PT1.3 is not configured as external pin button, it can help to enhance the anti-interference ability.

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2.2 PIN Diagram LQFP48

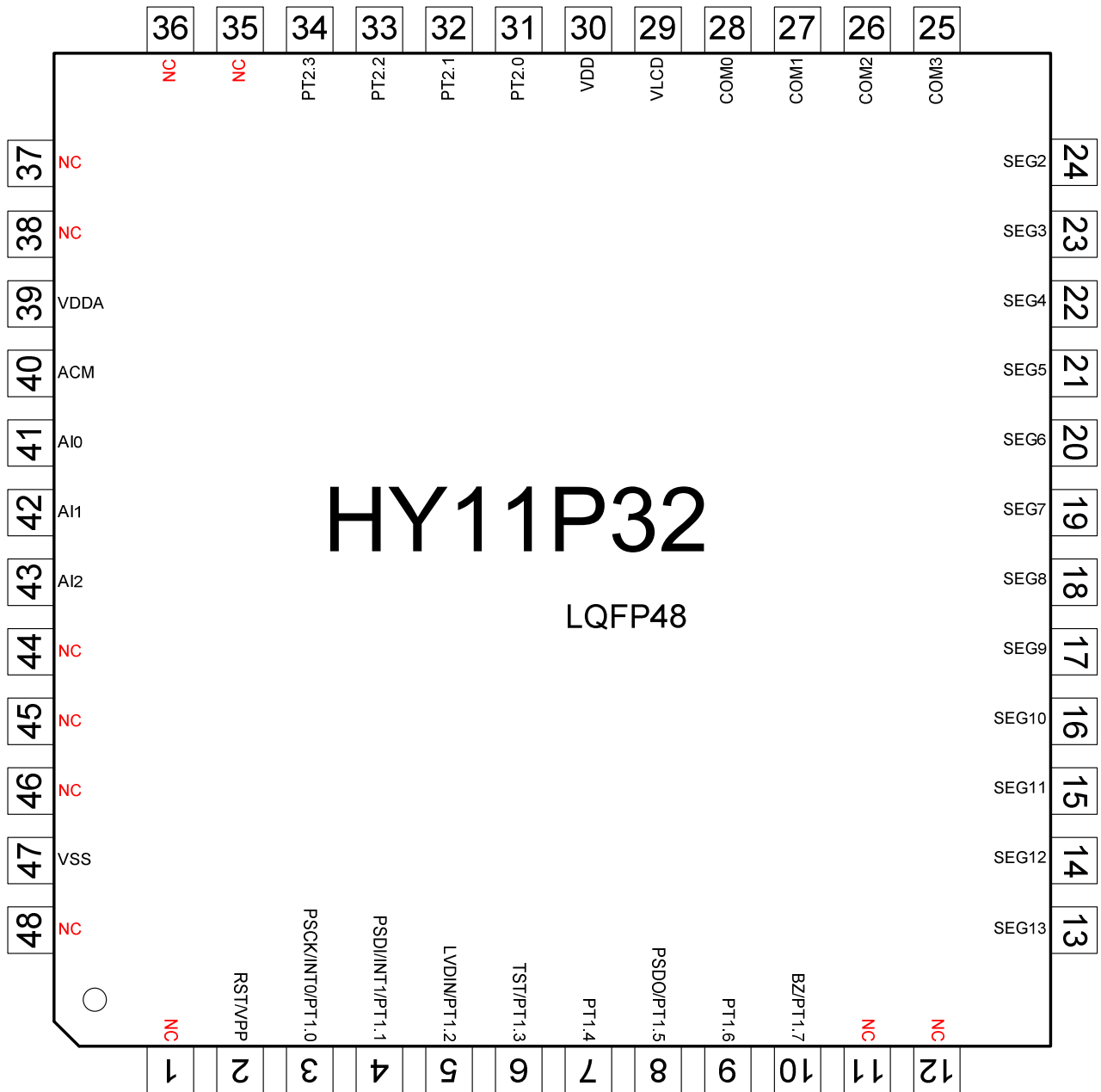


Figure 2-1 HY11P32 LQFP48 Pin Diagram

Note 1 : VPP and RST use the same pin. Input voltage cannot exceed 5.8V when not programming EPROM.

Note 2 : TST and PT1.3 use the same pin. Input voltage cannot exceed Vdd+0.3V while operating.

Note 3 : If PT1.3 is not configured as external pin button, it can help to enhance the anti-interference ability.

2.3 LQFP44 Pinout I/O Description

"I/O" input/output, "I" input, "O" output, "S" Smith Trigger, "C" CMOS features compatible input/output, "P" power supply, "A" analog channel

NO.	Pin Name	Pin Characteristic		Description
		Pin Type	Buffer Type	
1	RST	I	S	Reset IC
	VPP	P	P	EPROM programming voltage input
2	PT1.0	I	S	Digital input
	INT0	I	S	Interrupt input INT0
	PSCK	I	S	OTP programming interface SCK
3	PT1.1	I	S	Digital input
	INT1	I	S	Interrupt input INT0
	PSDI	I	S	OTP programming interface SDI
4	PT1.2	I	S	Digital input
	LVDIN	A	A	LVD external signal input pin
5	PT1.3	I	S	Digital input
	TST	I	S	Test Mode input pin (invalid)
6	PT1.4	I/O	S	Digital I/O
7	PT1.5	I/O	S	Digital I/O
	PSDO	O	C	OTP programming interface SDO
8	PT1.6	I/O	S	Digital I/O
9	PT1.7	I/O	S	Digital I/O
	BZ	O	C	Buzzer output
10	NC	-	-	Unused
11	SEG13	O	A	Segment output for LCD
12	SEG12	O	A	Segment output for LCD
13	SEG11	O	A	Segment output for LCD
14	SEG10	O	A	Segment output for LCD
15	SEG9	O	A	Segment output for LCD
16	SEG8	O	A	Segment output for LCD

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17	SEG7	O	A	Segment output for LCD
18	SEG6	O	A	Segment output for LCD
19	SEG5	O	A	Segment output for LCD
20	SEG4	O	A	Segment output for LCD
21	SEG3	O	A	Segment output for LCD
22	SEG2	O	A	Segment output for LCD
23	COM3	O	A	COM segment output for LDO
24	COM2	O	A	COM segment output for LDO
25	COM1	O	A	COM segment output for LDO
26	COM0	O	A	COM segment output for LDO
27	VLCD	P	P	Power supply for LCD
28	NC	-	-	Unused
29	VDD	P	P	Power supply for IC operation
30	PT2.0	I/O	S	Digital I/O
31	PT2.1	I/O	S	Digital I/O
32	PT2.2	I/O	C	Digital I/O
33	PT2.3	I/O	S	Digital I/O
34	NC	-	-	Unused
35	NC	-	-	Unused
36	VDDA	P	P	Regulator output, analog circuit voltage source
37	ACM	P	P	Internal analog circuit common ground pin
38	AI0	A	A	Analog input channel
39	AI1	A	A	Analog input channel
40	AI2	A	A	Analog input channel
41	NC	-	-	Unused
42	NC	-	-	Unused
43	NC	-	-	Unused
44	VSS	P	P	Grounding pin for IC operation voltage

Table 2-1 Pin Definition and Function Description

3. Application Circuit

3.1 Bridge Sensor I

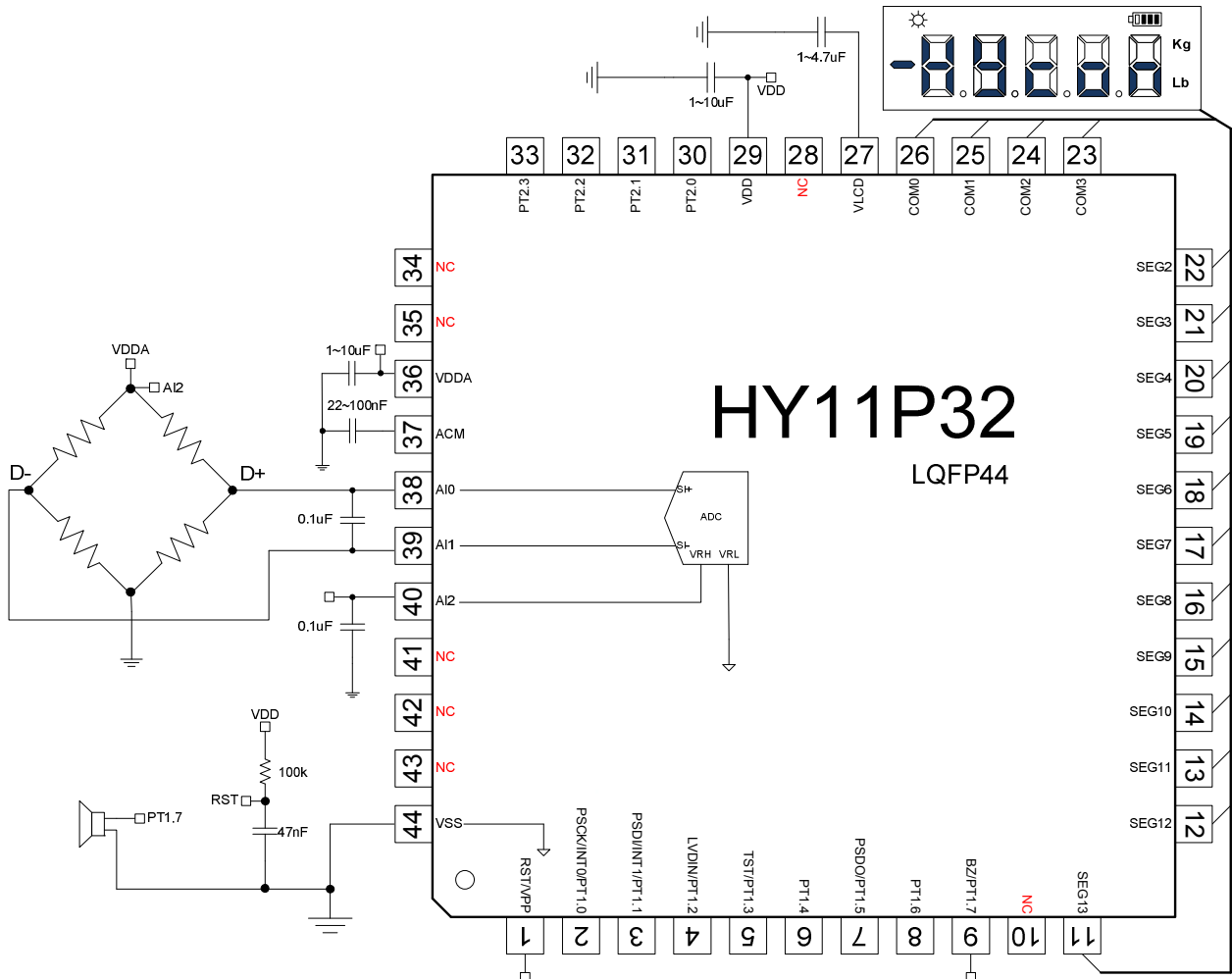


Figure 3-1 Bridge Sensor Application Circuit

Note 1 : DCSET[2:0] can conduct bias adjustment of Load Cell zero point voltage address

4. Function Outline

4.1 Internal Block Diagram

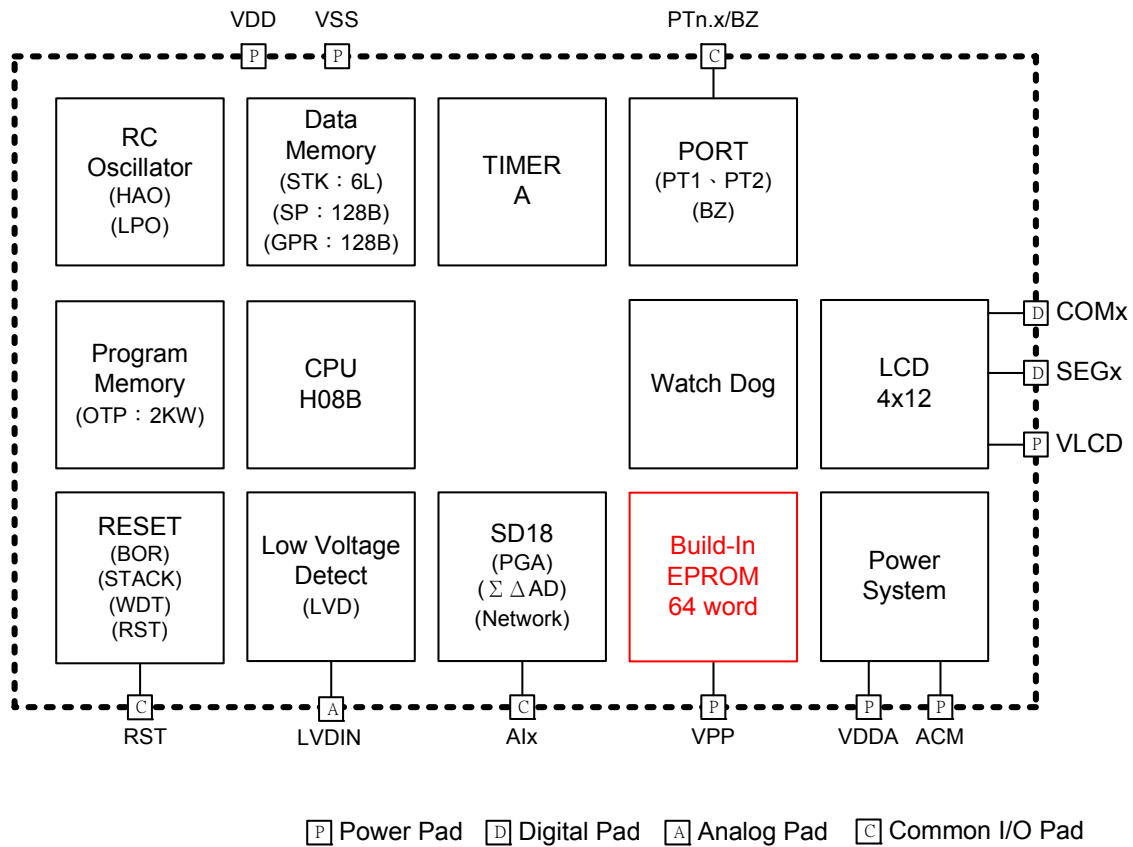


Figure 4-1 HY11P32 Internal Block Diagram

4.2 Related Description and Supporting Documents

IC Function Related Operating Instruction

- DS-HY11P32-Vxx HY11P32 Datasheet
- UG-HY11S14-Vxx HY11Pxx Series Users' Manual
- APD-CORE003-Vxx H08B Instruction Description

Development Tool Related Operating Instruction

- APD-HYIDE006-Vxx HY11xxx Series Development Tool Software Instruction Manual
- APD-HYIDE005-Vxx HY11xxx Series Development Tool Hardware Instruction Manual
- APD-OTP001-Vxx OTP Products Programming Pin Manual
- APD-HYIDE004-Vxx Product Production Related Operating Instruction
- APD-HYIDE004-Vxx HY1xxxx Series Production Line Specialized Programmer Manual
- BDI-HY11P32-Vxx HY11P32 Individual Product Die Bonding Information

4.3 SD18 Network

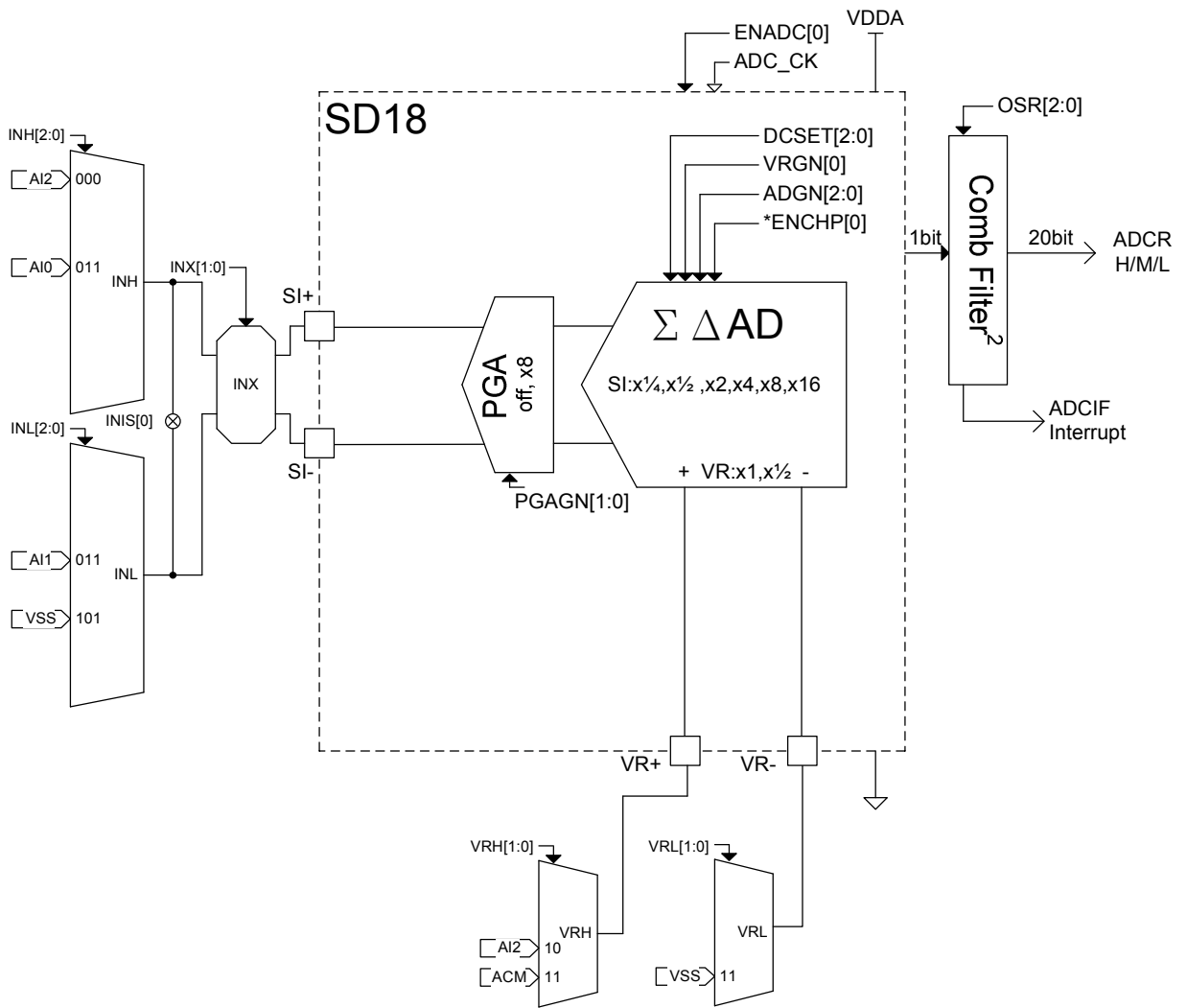


Figure 4-2 SD18 Network

6. Electrical Characteristics

Absolute maximum ratings over operating free-air temperature (unless otherwise noted)

Voltage applied at V_{DD} to V_{SS}	-0.2 V to 4.0 V
Voltage applied to any pin (see Note 1)	-0.2 V to $V_{DD} + 0.3$ V
Voltage applied to RST/VPP pin	-0.2 V to 6.9 V
Voltage applied to TST/PT1.3 pin (see Note 1)	-0.2 V to $V_{DD} + 1$ V
Diode current at any device terminal	± 2 mA
Storage temperature, Tstg: (unprogrammed device)	-55°C to 150°C
(programmed device)	-40°C to 85°C
Total power dissipation.	0.5w
Maximum output current sink by any PORT1 to PORT2 I/O pin.25mA

6.1 Recommended Operating Conditions

$T_A = -40^\circ\text{C} \sim 85^\circ\text{C}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
V_{DD}	Supply Voltage	All digital peripherals and CPU	2.2		3.6	V
		Analog peripherals	2.4		3.6	
V_{SS}	Supply Voltage		0		0	

6.2 Internal RC Oscillator

$T_A = 25^\circ\text{C}, V_{DD} = 3.0\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
HAO	High Speed Oscillator frequency	ENHAO[0]=1	1.6	2.0	2.4	MHz
LPO	Low Power Oscillator frequency	V_{DD} supply voltage be enable LPO	22	28	35	KHz

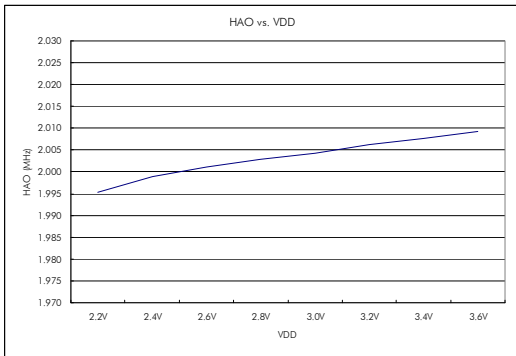


Figure 6.2-1 HAO vs. VDD

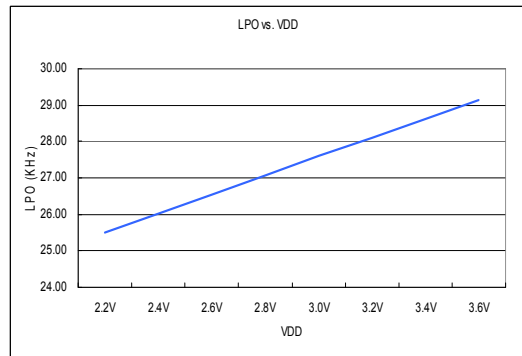


Figure 6.2-2 LPO vs. VDD

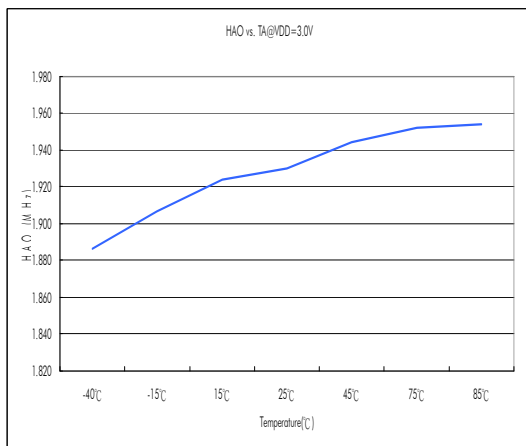


Figure 6.2-3 HAO vs. Temperature

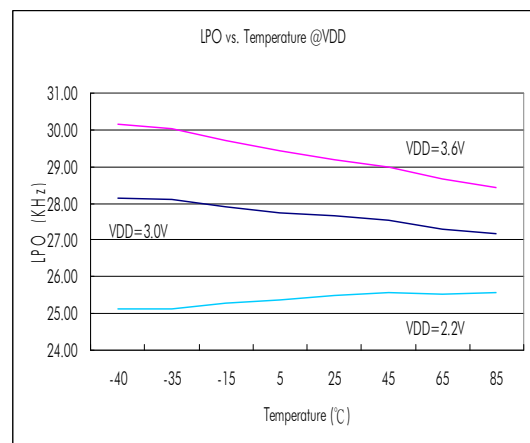


Figure 6.2-4 LPO vs. Temperature

6.3 Supply Current into VDD Excluding Peripherals Current

$T_A = 25^\circ\text{C}, V_{DD} = 3.0\text{V}, \text{OSC_LPO} = 28\text{KHz}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
I_{AM2}	Active mode 2	OSC_CY = off, OSC_HAO = 2MHz, CPU_CK = 2MHz		0.28	0.55	mA
I_{AM3}	Active mode 3	OSC_CY = off, OSC_HAO = 2MHz, CPU_CK = 1MHz		0.165	0.3	mA
I_{LP2}	Low Power 2	OSC_CY = off, OSC_HAO = off, CPU_CK = LPO, Idle state		1.65	3	μA
I_{LP3}	Low Power 3	OSC_CY = off, OSC_HAO = off, CPU_CK = off, Sleep state		0.65	1.2	μA

OSC_HAO : Internal High Accuracy Oscillator frequency.

CPU_CK : CPU core work frequency.

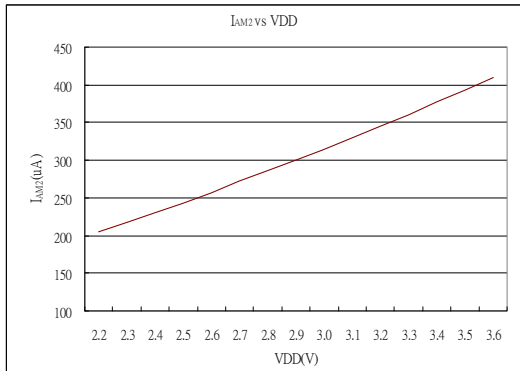


Figure 6.3-1 I_{AM2} vs. VDD

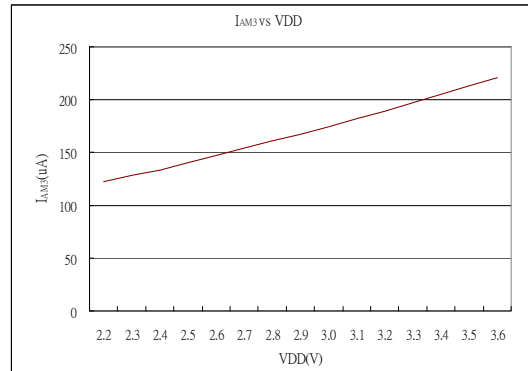


Figure 6.3-2 I_{AM3} vs. VDD

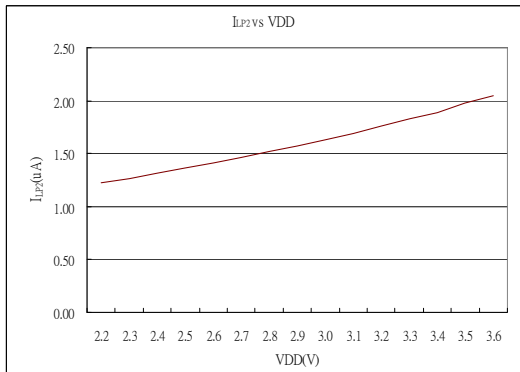


Figure 6.3-3 I_{LP2} vs. VDD

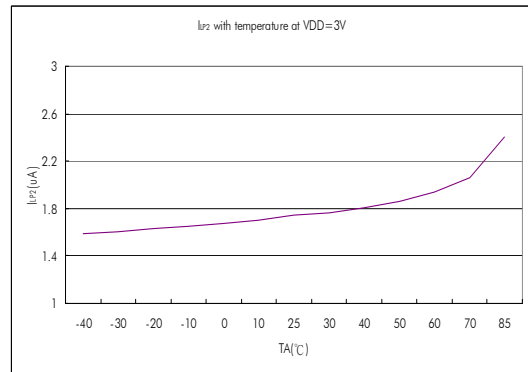


Figure 6.3-4 I_{LP2} vs. Temperature

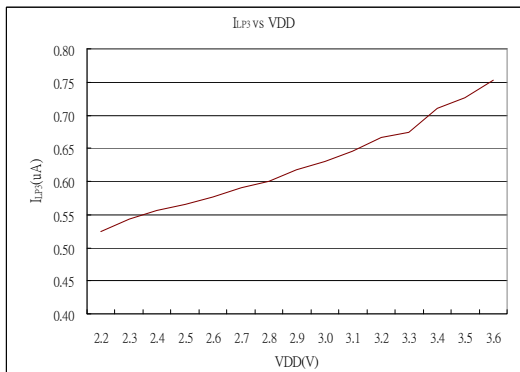


Figure 6.3-5 I_{LP3} vs. VDD

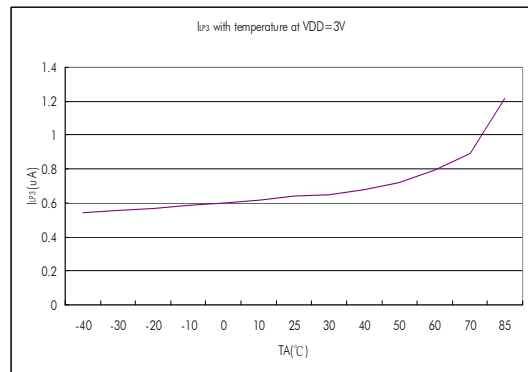


Figure 6.3-6 I_{LP3} vs. Temperature

6.4 Port1~2

$T_A = 25^\circ\text{C}, V_{DD} = 3.0\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
Input voltage and Schmitt trigger and leakage current and timing						
V_{IH}	High-Level input voltage				2.1	V
V_{IL}	Low-Level input voltage		0.9			
V_{hys}	Input Voltage hysteresis($V_{IH} - V_{IL}$)			0.8		V
I_{LKG}	Leakage Current				0.1	μA
R_{PU}	Port pull high resistance			180		$\text{k}\Omega$
Output voltage and current and frequency						
V_{OH}	High-level output voltage	$I_{OH}=10\text{mA}$	$V_{DD}-0.3$			V
V_{OL}	Low-level output voltage	$I_{OL}=-10\text{mA}$			$V_{SS}+0.3$	

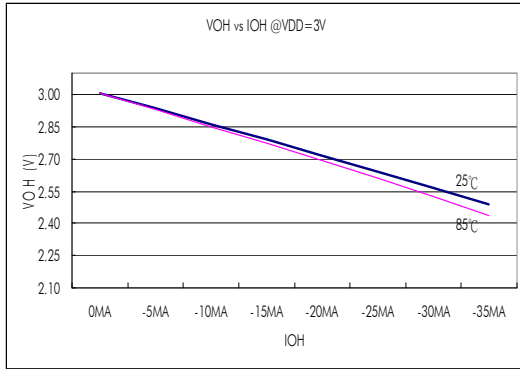


Figure 6.4-1 V_{OH} vs. I_{OH} @VDD=3.0V

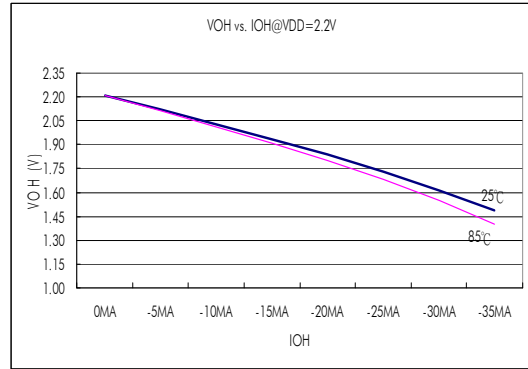


Figure 6.4-2 V_{OH} vs. I_{OH} @VDD=2.2V

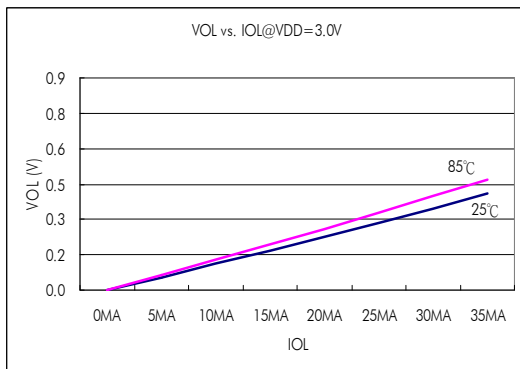


Figure 6.4-3 V_{OL} vs. I_{OL} @VDD=3.0V

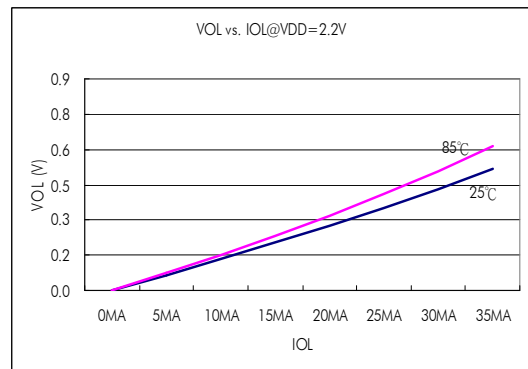


Figure 6.4-4 V_{OL} vs. I_{OL} @VDD=2.2V

6.5 Reset (Brownout, External RST pin, Low Voltage Detect)

$T_A = 25^\circ\text{C}, V_{DD} = 3.0\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit	
BOR	Pulse length needed to accepted reset internally, t_{d-LVR}		2			us	
	V_{DD} Start Voltage to accepted reset internally (L \rightarrow H), V_{LVR}		1.6	1.85	2.1	V	
	Hysteresis, $V_{HYS-LVR}$			70		mV	
RST	Pulse length needed as RST/VPP pin to accepted reset internally, t_{d-RST}		2			us	
	Input Voltage to accepted reset internally		0.9			V	
	Hysteresis, $V_{HYS-RST}$			0.8		V	
LVD	Operation current, I_{LVD}			10	15	uA	
	External input voltage to compare reference voltage			1.2		V	
	Compare reference voltage temperature drift	$T_A = -40^\circ\text{C} \sim 85^\circ\text{C}$		100		ppm/ $^\circ\text{C}$	
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1110b$			3.3		V	
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1101b$			3.2			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1100b$			3.1			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1011b$			3.0			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1010b$			2.9			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1001b$			2.8			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1000b$			2.7			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0111b$			2.6			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0110b$			2.5			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0101b$			2.4			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0100b$			2.3			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0011b$			2.2			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0010b$			2.1			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0001b$			2.0			
BOR : Brownout Reset LVR : Low Voltage Reset of BOR LVD : Low Voltage Detect RST : External Reset pin							

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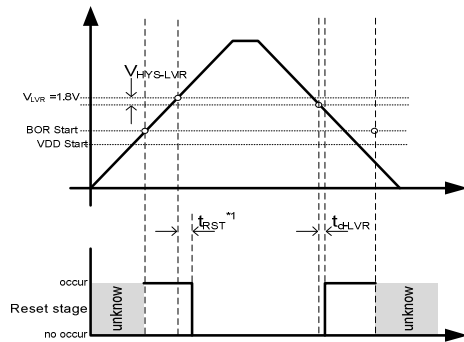


Figure 6.5-1 BOR reset diagram

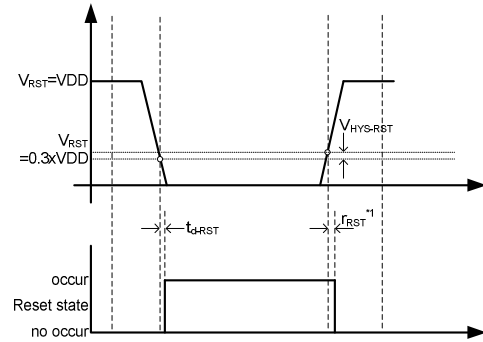


Figure 6.5-2 RST reset diagram

*1 t_{RST} : Please see BOR Introduce of HY11Pxx series User's Guide (UG-HY11S14-Vxx).

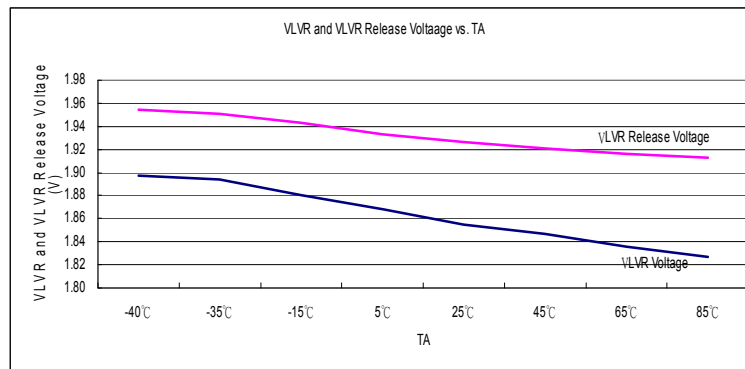


Figure 6.5-3 LVR vs. Temperature

6.6 Power System

$T_A = 25^\circ\text{C}, V_{DD} = 3.0\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions		Min.	Typ.	Max.	unit
VDDA	VDDA operation current, I_{VDDA}	$I_L = 0\text{mA}$	VDDAX[1:0]=00b	22			μA
	Select VDDA output voltage	$I_L = 0.1\text{mA}$, $V_{DD} \geq V_{DDA} + 0.2\text{V}$	VDDAX [1:0]=11b	2.4			V
	Dropout voltage	$I_L = 10\text{mA}$	VDDAX [1:0]=11b	180			mV
	Temperature drift	VDDAX [1:0]=11b	$T_A = -40^\circ\text{C} \sim 85^\circ\text{C}$	50			ppm/ $^\circ\text{C}$
	V_{DD} Voltage drift	$I_L = 0.1\text{mA}$	$V_{DD} = 2.5\text{V} \sim 3.6\text{V}$	± 0.2			%/V
ACM	ACM operation current, I_{ACM}	$I_L = 0\text{mA}$		20			μA
	Output voltage, V_{ACM}	ENACM[0]=1	$I_L = 0\mu\text{A}$	1.0			V
	Output voltage with Load		$I_L = \pm 200\mu\text{A}$	0.98	1.02		V_{ACM}
	Temperature drift	ENACM[0]=1,	$T_A = -40^\circ\text{C} \sim 85^\circ\text{C}$	50			ppm/ $^\circ\text{C}$
	VDDA Voltage drift	$I_L = 10\mu\text{A}$		100			$\mu\text{V}/\text{V}$

VDDA : Adjust Voltage Regulator
ACM : Analog Common Mode Voltage

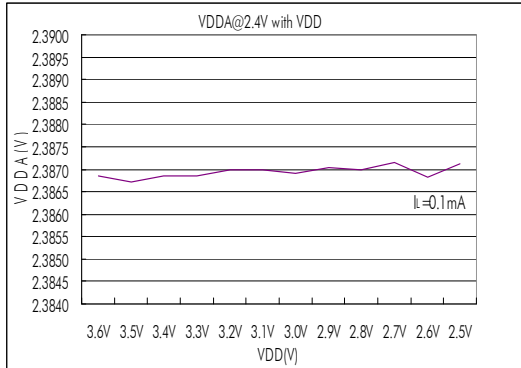


Figure 6.6-1 VDDA $I_L = 0.1\text{mA}$ vs. VDD

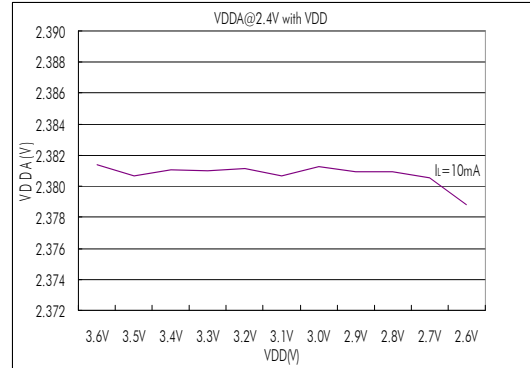


Figure 6.6-3 VDDA $I_L = 10\text{mA}$ vs. VDD

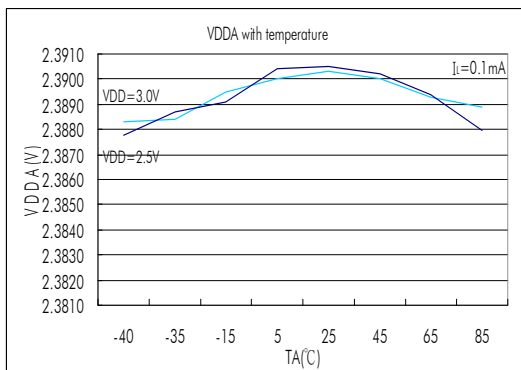


Figure 6.6-2 VDDA $I_L = 0.1\text{mA}$ vs. Temperature

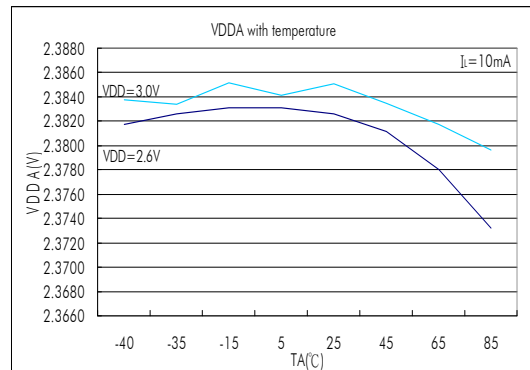


Figure 6.6-4 VDDA $I_L = 10\text{mA}$ vs. Temperature

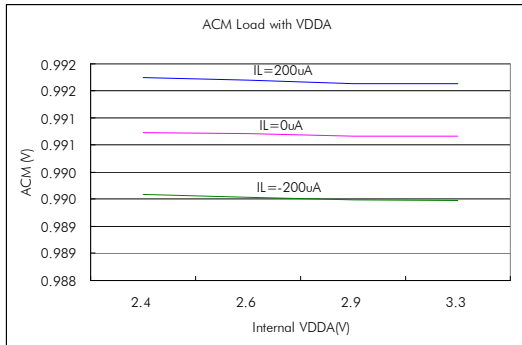


Figure 6.6-5 ACM Load vs. VDDA

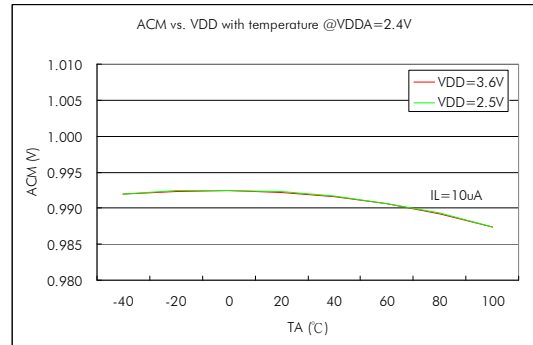


Figure 6.6-6 ACM vs. Temperature

6.7 LCD

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{V}$, $C_{VLCD} = 4.7\mu\text{F}$, unless otherwise noted.

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit	
I_{LCD}	Operation supply current without output buffer.(all segment turn on)	LCDPR[0]=1	$V_{DD} = 2.2\text{V}$	20		μA	
			$V_{DD} = 3.0\text{V}$				
VLCD	Supply Voltage at VLCD pin	LCDPR[0]=0	2.2		3.6	V	
	Embedded Charge Pump output voltage at VLCD pin	$V_{DD} = 2.2\text{V}$, LCDPR[0]=1, $C_{VLCD} = 4.7\mu\text{F}$	VLCDX[1:0]=11b	2.295	2.55	2.805	V
			VLCDX[1:0]=10b	2.52	2.8	3.08	
			VLCDX[1:0]=01b	2.745	3.05	3.355	
			VLCDX[1:0]=00b	2.97	3.3	3.63	
Z_{LCD}	Output impedance with LCD buffer	$f_{LCD} = 128\text{Hz}$, VLCD=3.05V		10		$\text{k}\Omega$	

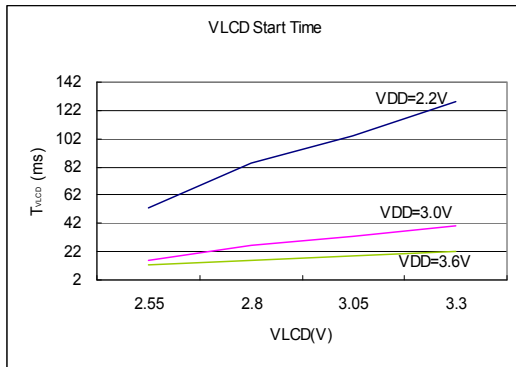


Figure 6.7-1 LCD Start Time

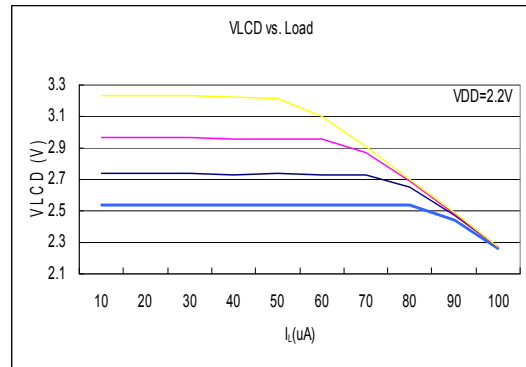


Figure 6.7-2 VLCD vs. I_L @ VDD=2.2V

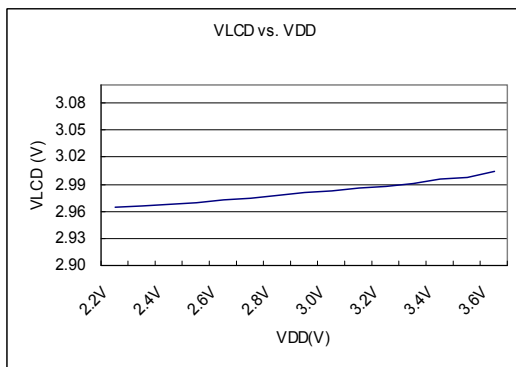


Figure 6.7-3 VLCD vs. VDD

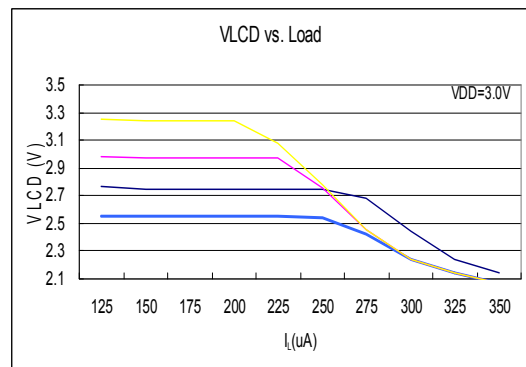


Figure 6.7-4 VLCD vs. I_L @ VDD=3.0V

6.8 SD18, Power Supply and Recommended Operating Conditions

$T_A = 25^\circ\text{C}, V_{DD} = 3.0\text{V}, V_{DDA}=2.4\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions		Min.	Typ.	Max.	unit
V_{SD18}	Supply Voltage at VDDA	ENVDDA[0]=0		2.4		3.6	V
f_{SD18}	Modulator sample frequency, ADC_CK			25	250	300	KHz
	Over Sample Ratio, OSR			256		32768	
I_{SD18}	Operation supply current without PGA	ENADC[0]=1 INBUF[0]=0,VRBUF[0]=0	GAIN =4, ADC_CK=250KHz		120		μA

6.8.1 PGA, Power Supply and Recommended Operating Conditions

$T_A = 25^\circ\text{C}, V_{DD} = 3.0\text{V}, V_{DDA}=2.4\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions		Min.	Typ.	Max.	unit
V_{PGA}	Supply Voltage at VDDA	ENVDDA[0]=0		2.4		3.6	V
I_{PGA}	Operation supply current	PGAGN[1:0]=<11>			320		μA
G_{PGA}	Gain temperature drift	$T_A = -40^\circ\text{C} \sim 85^\circ\text{C}$	GAIN=128		15		ppm/ $^\circ\text{C}$

6.8.2 SD18, Performance II ($f_{SD18}=250\text{KHz}$)

$T_A = 25^\circ\text{C}, V_{DD} = 3.0\text{V}, V_{DDA}=2.9\text{V}, V_{VR}=1.0\text{V}, \text{GAIN}=1$ without PGA, unless otherwise noted

Sym.	Parameter	Test Conditions		Min.	Typ.	Max.	unit
INL	Integral Nonlinearity(INL)	$V_{DDA}=2.4\text{V}, V_{VR}=1.0\text{V}, \Delta\text{SI}=\pm 200\text{mV}$			± 0.003	± 0.01	%FSR
		$V_{DDA}=2.4\text{V}, V_{VR}=1.0\text{V}, \Delta\text{SI}=\pm 450\text{mV}$					
	No Missing Codes ³	ADC_CK=250KHz, OSR[2:0]=010b		19			Bits
G_{SD18}	Temperature drift Gain 1~x16 (INBUF[0]=0b,)	INBUF[0]=0b,VRBUF[0]=0b	$T_A = -40^\circ\text{C} \sim 85^\circ\text{C}$		10		ppm/ $^\circ\text{C}$
E_{OS}	Offset error of Full Scale Rang input voltage range with Chopper without PGA	$\Delta\text{AI}=0\text{V}$ $\Delta\text{VR}=0.9\text{V}$ DCSET[2:0]=<000> * ΔAI is external short	Gain=2			1	%FSR
			GAIN=1		2		$\mu\text{V}/^\circ\text{C}$
	GAIN=2		1				
	GAIN=4		0.5				
	GAIN=16		0.15				
CM_{SD18}	Common-mode rejection	$V_{CM}=0.7\text{V}$ to 1.7V, $V_{VR}=1.0\text{V}$, without PGA	$V_{SI}=0\text{V}$, GAIN=1		90		dB
		$V_{CM}=0.7\text{V}$ to 1.7V, $V_{VR}=1.0\text{V}$, without PGA	$V_{SI}=0\text{V}$, GAIN=16		75		

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PSRR	DC power supply rejection	VDDA=3.0V, Δ VDDA=±100mV, V _{VR} =1.0V, V _{SI} =1.2V, V _{SII} =1.2V,	GAIN=1	75	dB
			PGA=off		
			GAIN=16		
			PGA=8		

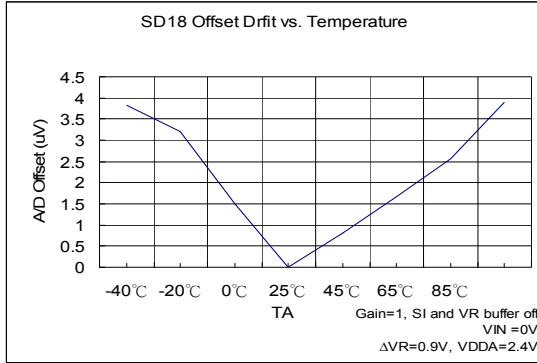


Figure 6.8-1(a) SD18 Offset Temperature Drift

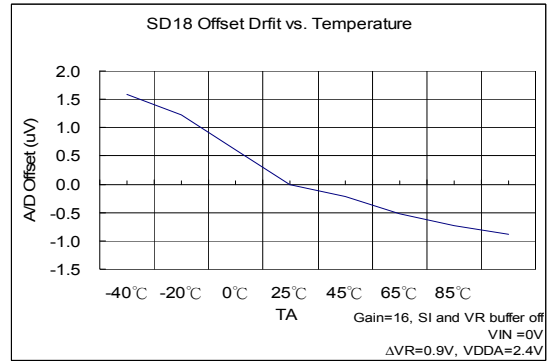


Figure 6.8-1(b) SD18 Offset Temperature Drift

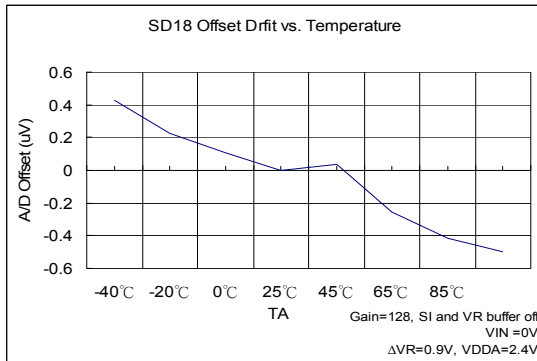


Figure 6.8-1(c) SD18 Offset Temperature Drift

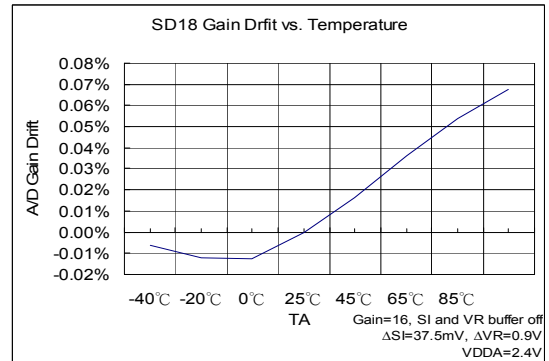


Figure 6.8-2(a) SD18 Gain Drift with Temperature

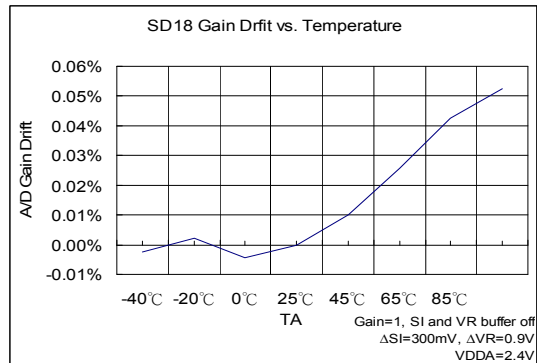


Figure 6.8-2(b) SD18 Gain Drift with Temperature

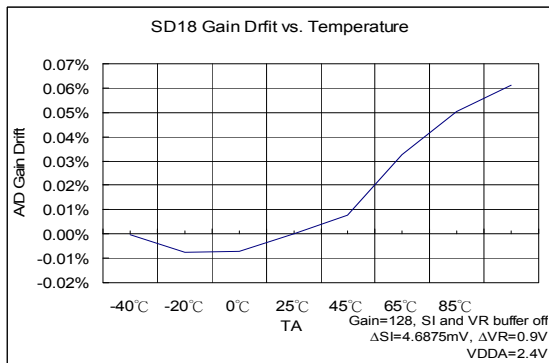


Figure 6.8-2(c) SD18 Gain Drift with Temperature

6.8.3 SD18 Noise Performance

$T_A = 25^\circ\text{C}, V_{DD} = 3.0\text{V}, V_{DDA}=2.4\text{V},$ unless otherwise noted

HY11P32 provides important input noise specification that aims at SD18. Table6.8-3(a) and Table6.8-3(b) lists out the relations of typical noise specification, Gain, Output rate, and maximum input voltage of single end. Test condition configuration and external input signal short, voltage reference: 1.2V and 1024 records were sampled.

ENOB(RMS) with OSR/GAIN at A/D Clock=250Khz, VDDA=2.4V, VREF=1.2V													
Max. Vin(mV) =0.9*VREF ⁽¹⁾	OSR				256	512	1024	2048	4096	8192	16384	32768	
	Output rate(HZ)				977	488	244	122	61	31	15	8	
	Gain	=	PGA	x	ADGN								
± 2400	0.25	=	1	x	0.25	16.14	17.41	18.04	18.47	18.80	19.06	19.23	19.31
± 2160	0.5	=	1	x	0.5	16.15	17.41	18.03	18.42	18.75	19.13	19.24	19.30
± 1080	1	=	1	x	1	16.12	17.35	17.98	18.37	18.74	19.02	19.24	19.34
± 540	2	=	1	x	2	16.06	17.18	17.80	18.20	18.64	18.98	19.17	19.32
± 270	4	=	1	x	4	15.97	16.97	17.57	17.98	18.44	18.79	19.05	19.20
± 135	8	=	1	x	8	15.79	16.66	17.20	17.70	18.16	18.50	18.85	19.10
± 68	16	=	1	x	16	15.53	16.30	16.79	17.36	17.79	18.26	18.60	18.87
± 8	128	=	8	x	16	13.84	14.35	14.87	15.33	15.85	16.38	16.85	17.28

(1) Max.Vin (mV) is the max. input voltage of single end to ground (VSS).

Table6.8-3(a) SD18 ENOB Table

RMS Noise(uV) with OSR/GAIN at A/D Clock=250Khz, VDDA=2.4V, VREF=1.2V													
Max. Vin(mV) =0.9*VREF	OSR				256	512	1024	2048	4096	8192	16384	32768	
	Output rate(HZ)				977	488	244	122	61	31	15	8	
	Gain	=	PGA	x	ADGN								
± 2400	0.25	=	1	x	0.25	133.39	55.79	35.80	26.52	21.22	17.56	15.68	14.77
± 2160	0.5	=	1	x	0.5	66.41	27.72	18.10	13.82	11.01	8.37	7.75	7.45
± 1080	1	=	1	x	1	33.93	14.45	9.32	7.11	5.51	4.53	3.88	3.62
± 540	2	=	1	x	2	17.68	8.15	5.28	4.00	2.96	2.32	2.04	1.84
± 270	4	=	1	x	4	9.42	4.69	3.10	2.34	1.69	1.32	1.11	1.00
± 135	8	=	1	x	8	5.33	2.91	2.00	1.41	1.03	0.81	0.64	0.54
± 68	16	=	1	x	16	3.17	1.87	1.33	0.90	0.66	0.48	0.38	0.31
± 8	128	=	8	x	16	1.28	0.90	0.63	0.46	0.32	0.22	0.16	0.12

Table6.8-3(b) SD18 RMS Noise Table

The RMS noise are referred to the input. The Effective Number of Bits (ENOB(RMS Bit)) is defined as:

$$\text{ENOB(RMS)} = \frac{\ln\left(\frac{\text{FSR}}{\text{RMS Noise}}\right)}{\ln(2)}$$

$$\text{RMS Noise} = \frac{\left(2 \times \text{VREF} \times \sqrt{\sum_{k=1}^{1024} (\text{ADO}[k] - \text{Average})^2}\right)}{2^{23}}$$

Where FSR (Full - Scale Range) = $2 \times \text{VREF}/\text{Gain}$.

$$\text{Average} = \frac{\sum_{k=1}^{1024} (\text{ADO}[k])}{1024}$$

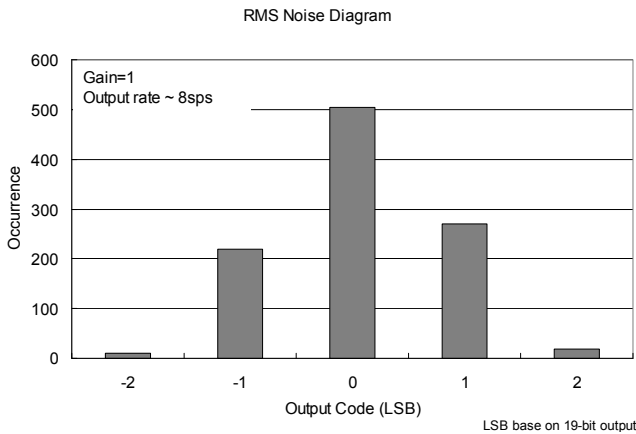


Figure 6.8-3(a) RMS Noise Diagram

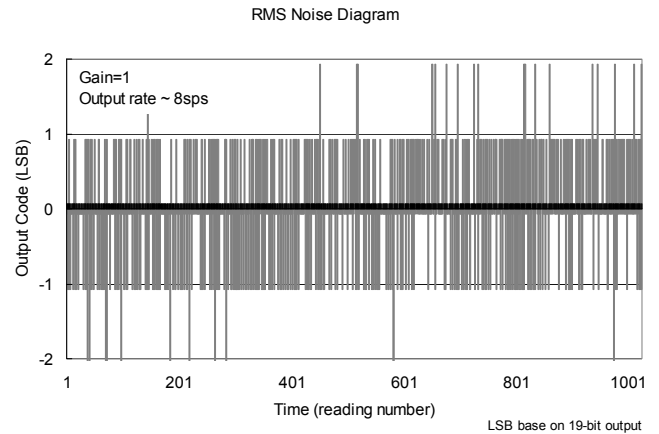


Figure 6.8-3(b) Output Code Diagram

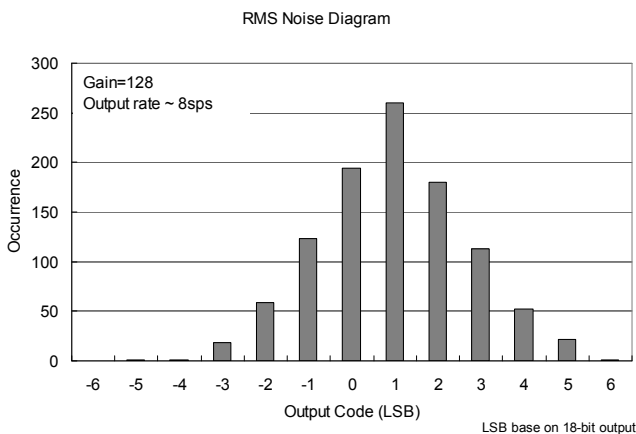


Figure 6.8-3(c) RMS Noise Diagram

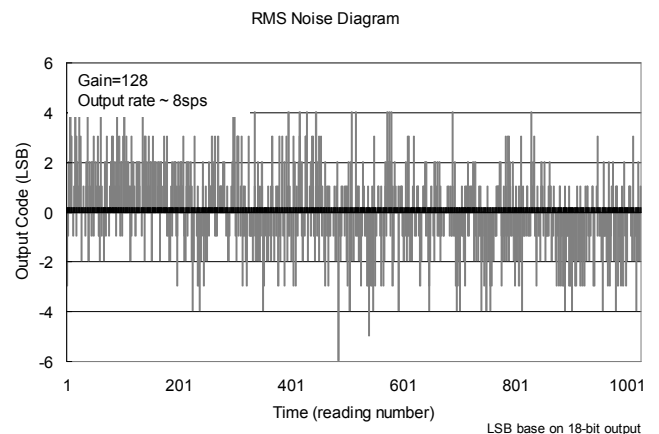


Figure 6.8-3(d) Output Code Diagram

6.9 Built-in EPROM (BIE)

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
V_{BIE}	Supply Voltage			6.0	6.5	V
I_{BIE}	Operation supply current			5		mA
V_{SS}	Supply Voltage			0		V

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7. Ordering Information

Device No. ¹	Package Type	Pins	Package Drawing		Code ²	Shipment Packing Type	Unit Q'ty	Material Composition	MSL ³
HY11P32-D000	Die	-	D	000	000	-	250	Green ⁴	-
HY11P32-L044	LQFP	44	L	044	000	Tray	160	Green ⁴	MSL-3
HY11P32-L048	LQFP	48	L	048	000	Tray	250	Green ⁴	MSL-3

¹ **Device No.:** Model No. – Package Type Description – Code (Blank Code/ Standard/ Customized Programming Code)

Ex: Your customized programming code is 008 and you require die shipment.

The device No. will be HY11P32-D000-008.

Ex: You request blank code in die package.

The device No. will be HY11P32-D000.

Ex: You request blank code in LQFP 44 package.

The device No. will be HY11P32-L044.

And please clearly indicate the shipment packing type when placing orders.

Ex: Your customized programming code is 009 and you require products in LQFP 48 package.

The device No. will be HY11P32-L048-009.

And please clearly indicate the shipment packing type when placing orders.

² **Code:**

“001”~ “999” is standard or customized programming code. Blank code does not have these numbers.

³ **MSL:**

The Moisture Sensitivity Level ranking conforms to IPC/JEDEC J-STD-020 industry standard categorization. The products are processed, packed, transported and used with reference to IPC/JEDEC J-STD-033.

⁴ **Green (RoHS & no Cl/Br):**

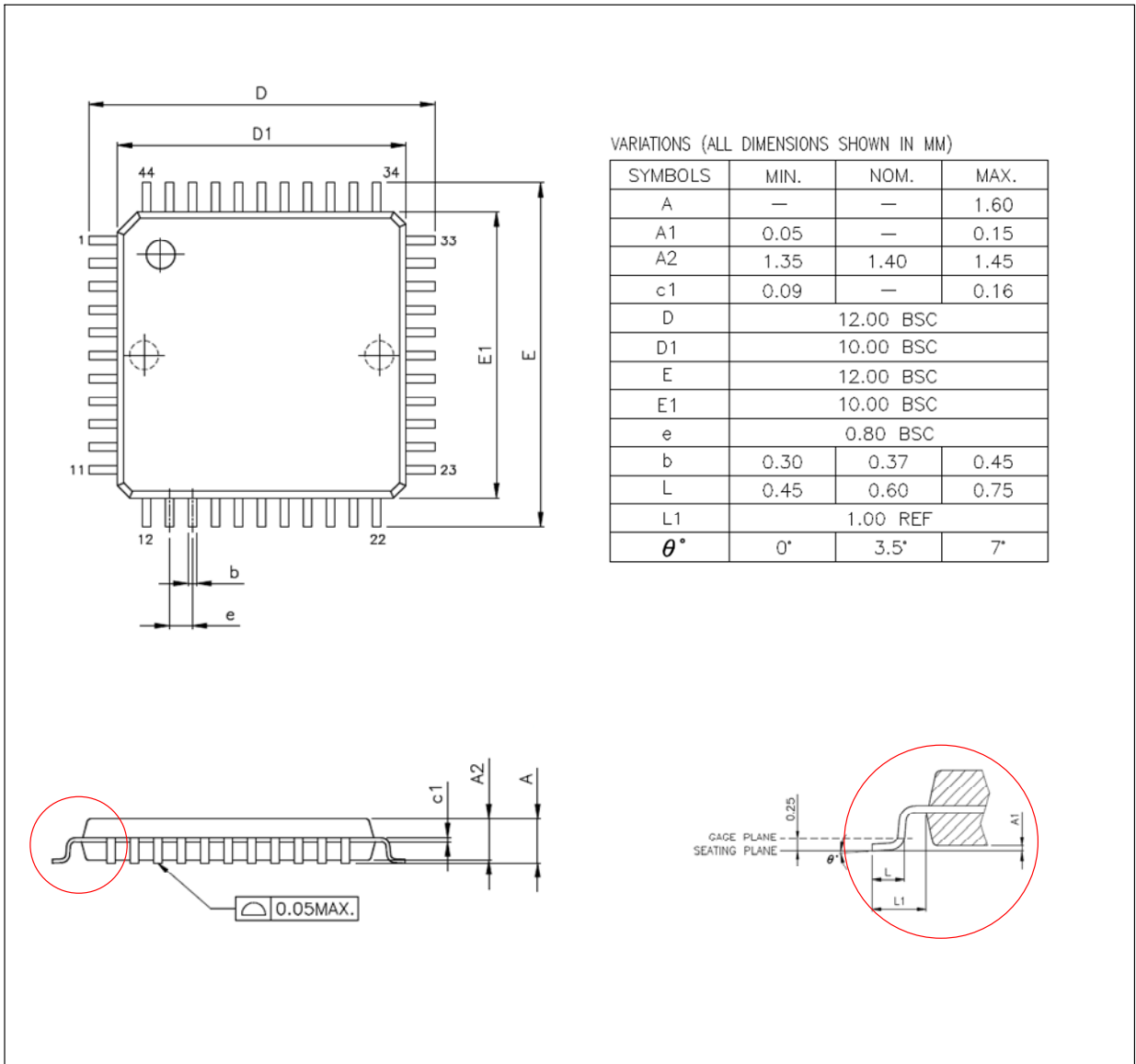
HYCON products are Green products that compliant with RoHS directive and are Halogen free (Br/Cl<0.1%)

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8. Package Information

8.1 LQFP44(L044)

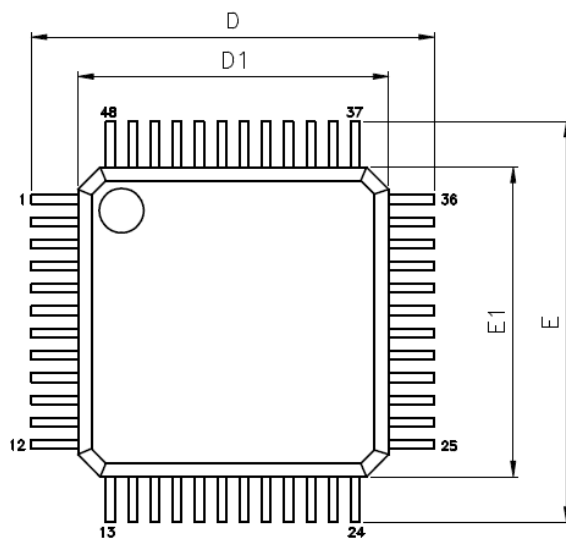


JEDEC MS-026 compliant

HY11P32

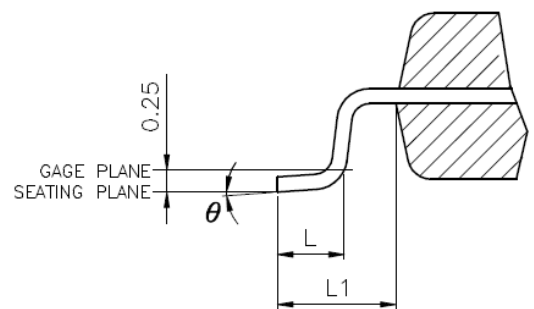
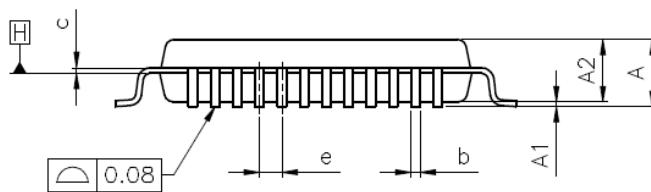
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8.2 LQFP48(L048)



VARIATIONS (ALL DIMENSIONS SHOWN IN MM)

SYMBOLS	MIN.	NOM.	MAX.
A	--	--	1.60
A1	0.05	--	0.15
A2	1.35	1.40	1.45
b	0.17	0.22	0.27
c	0.09	--	0.20
D	9.00 BSC		
D1	7.00 BSC		
E	9.00 BSC		
E1	7.00 BSC		
e	0.50 BSC		
L	0.45	0.60	0.75
L1	1.00 REF		
θ	0°	3.5°	7°



JEDEC MS-026 compliant

9. Revision Record

Major differences are stated thereafter:

Version	Page	Revision Summary
V03	ALL	First edition
V08	1	Title Revised
	6	Add in LVDIN function of PT1.2
	7	Add in LVDIN function of PT1.2
	9	Add in LVDIN function of PT1.2
	10	Revise the content of block diagram, WDT reset is 00H
	11	Add in Chapter 4.3 SD18 Network
	12	Revise register list, add in LVDIN function of PT1.2
	14	HAO spec revised, 2MHz \pm 20%
	17	Add in LVDIN function of PT1.2
	23	Revise Figure 6.8 content and order
V12	5	Revise Chapter 1 Features Content
	11	Revise Figure 4.1 and 4.2 Development Tool Related Operating Instruction serial numbers
	14	Revise Chapter 6 Electrical Characteristics Content
	20	Revise Power System Temperature Drift Spec
	25~26	Add in Chapter 6.8.3 SD18 Noise Performance
	28	Chapter 7 Ordering information revision